

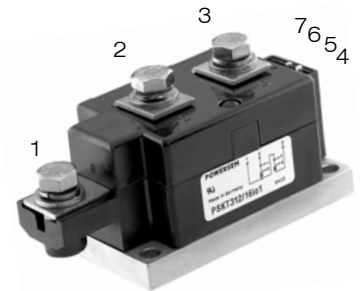
Thyristor Modules Thyristor/Diode Modules

PSKT 312
PSKH 312

$I_{TRMS} = 2 \times 520 \text{ A}$
 $I_{TAVM} = 2 \times 320 \text{ A}$
 $V_{RRM} = 1200-1800 \text{ V}$

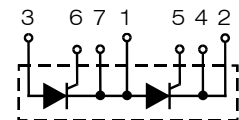
Preliminary Data Sheet

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type	
1300	1200	PSKT 312-12io1	PSKH 312-12io1
1500	1400	PSKT 312-14io1	PSKH 312-14io1
1700	1600	PSKT 312-16io1	PSKH 312-16io1
1900	1800	PSKT 312-18io1	PSKH 312-18io1

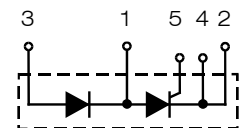


Symbol	Test Conditions	Maximum Ratings	
I_{TRMS}, I_{FRMS} I_{TAVM}, I_{FAVM}	$T_{VJ} = T_{VJM}$ $T_C = 85^\circ\text{C}; 180^\circ \text{ sine}$	520 320	A A
I_{TSM}, I_{FSM}	$T_{VJ} = 45^\circ\text{C};$ $V_R = 0$ $t = 10 \text{ ms (50 Hz)}$ $t = 8.3 \text{ ms (60 Hz)}$	9200 10100	A A
	$T_{VJ} = T_{VJM}$ $V_R = 0$ $t = 10 \text{ ms (50 Hz)}$ $t = 8.3 \text{ ms (60 Hz)}$	8000 8800	A A
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$ $t = 10 \text{ ms (50 Hz)}$ $t = 8.3 \text{ ms (60 Hz)}$	423 000 423 000	A^2s A^2s
	$T_{VJ} = T_{VJM}$ $V_R = 0$ $t = 10 \text{ ms (50 Hz)}$ $t = 8.3 \text{ ms (60 Hz)}$	320 000 321 000	A^2s A^2s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 50 \text{ Hz}, t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 1 \text{ A},$ $di_G/dt = 1 \text{ A}/\mu\text{s}$ repetitive, $I_T = 960 \text{ A}$ non repetitive, $I_T = I_{TAVM}$	100 500	$\text{A}/\mu\text{s}$ $\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}; V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty; \text{method 1 (linear voltage rise)}$	1000	$\text{V}/\mu\text{s}$
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$ $t_p = 30 \mu\text{s}$ $t_p = 500 \mu\text{s}$	120 60 20 10	W W W V
P_{GAV} V_{RGM}			
T_{VJ}		-40...+140	$^\circ\text{C}$
T_{VJM}		140	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	3000 3600	V~ V~
M_d	Mounting torque (M6) Terminal connection torque (M8)	4.5-7/40-62 Nm/lb.in. 11-13/97-115 Nm/lb.in.	
Weight	Typical including screws	750	g

PSKT



PSKH



Features

- International standard package
- Direct copper bonded Al_2O_3 -ceramic with copper base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered E 148688
- Keyed gate/cathode twin pins

Applications

- Motor control, softstarter
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Solid state switches

Advantages

- Simple mounting
- Improved temperature and power cycling capability
- Reduced protection circuits

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

Symbol	Test Conditions	Characteristic Values
I_{RRM}, I_{DRM}	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	40 mA
V_T, V_F	$I_T, I_F = 600 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.32 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 140^\circ\text{C}$)	0.8 V
r_T		0.68 m Ω
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	2 V
	$T_{VJ} = -40^\circ\text{C}$	3 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	150 mA
	$T_{VJ} = -40^\circ\text{C}$	220 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	0.25 V
I_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	10 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 30 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	200 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	150 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 1 \text{ A}; di_G/dt = 1 \text{ A}/\mu\text{s}$	2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 300 \text{ A}; t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ typ. $V_R = 100 \text{ V}; dv/dt = 50 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	200 μs
Q_S	$T_{VJ} = 125^\circ\text{C}; I_T, I_F = 300 \text{ A}; -di/dt = 50 \text{ A}/\mu\text{s}$	760 μC
I_{RM}		275 A
R_{thJC}	per thyristor (diode); DC current per module	0.12 K/W
R_{thJK}	per thyristor (diode); DC current per module	0.06 K/W
	other values see Fig. 8/9	0.16 K/W
		0.08 K/W
d_s	Creeping distance on surface	12.7 mm
d_A	Creepage distance in air	9.6 mm
a	Maximum allowable acceleration	50 m/s ²

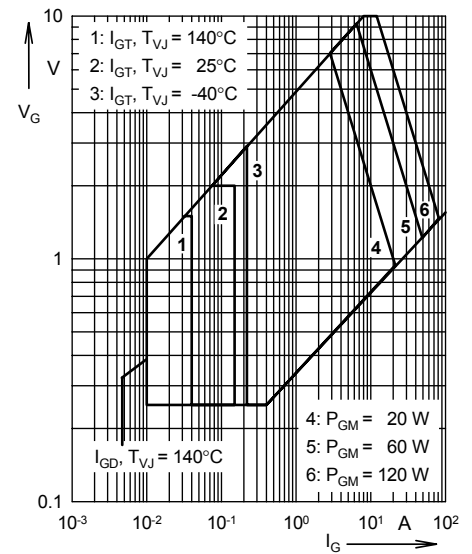


Fig. 1 Gate trigger characteristics

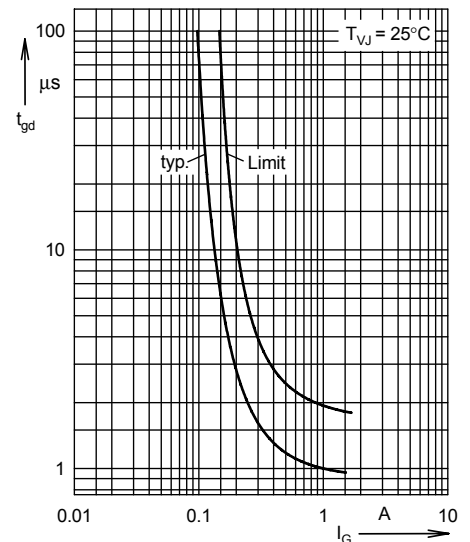
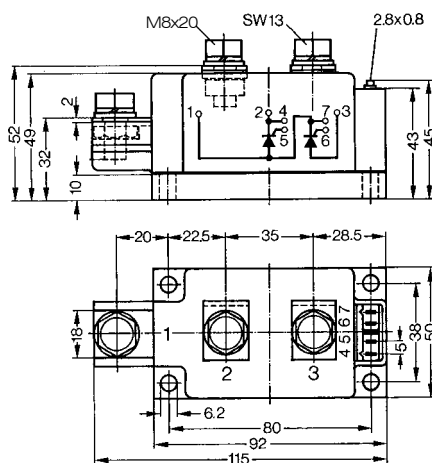


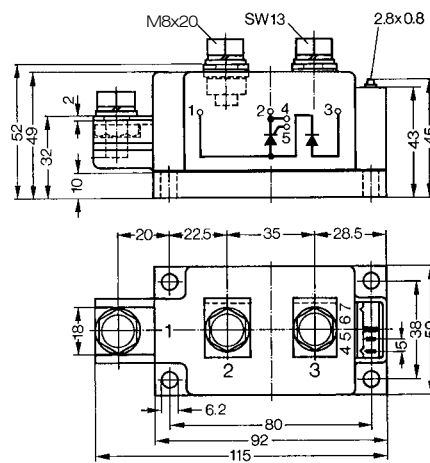
Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")

PSKT



PSKH



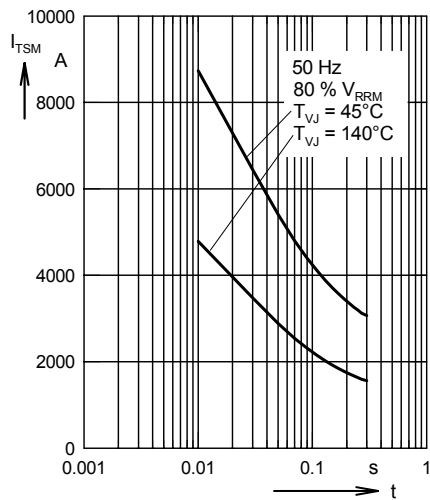


Fig. 3 Surge overload current
 I_{TSM} , I_{FSM} : Crest value, t : duration

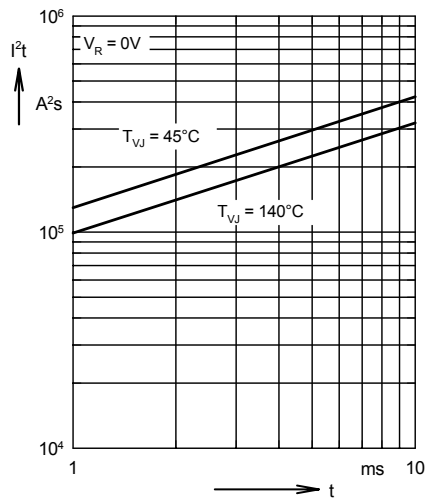


Fig. 4 I^2t versus time (1-10 ms)

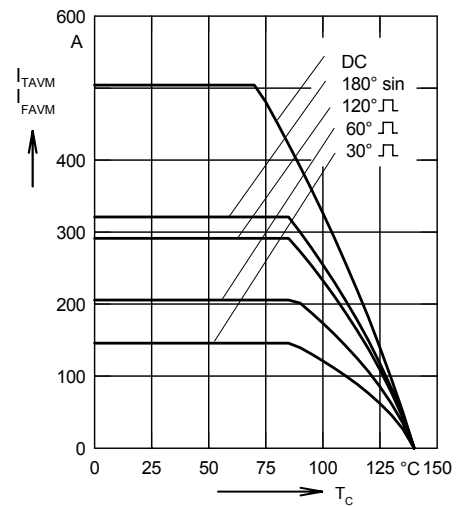


Fig. 4a Maximum forward current at case temperature

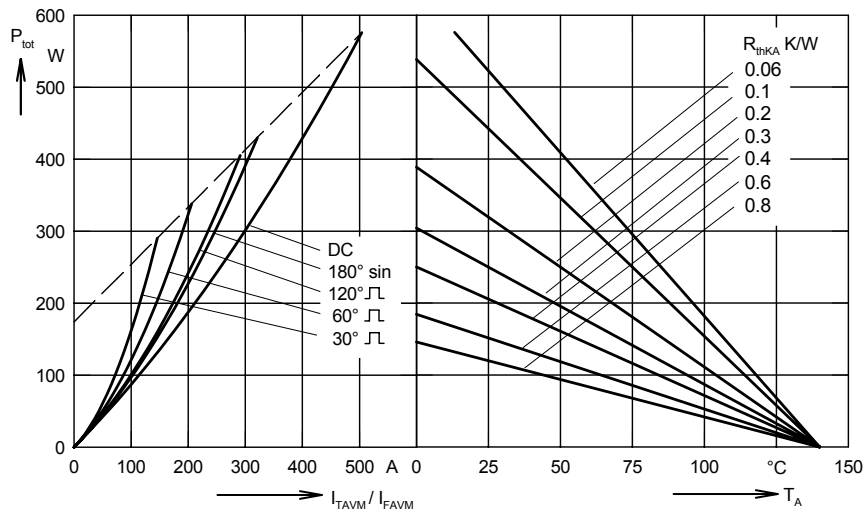


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

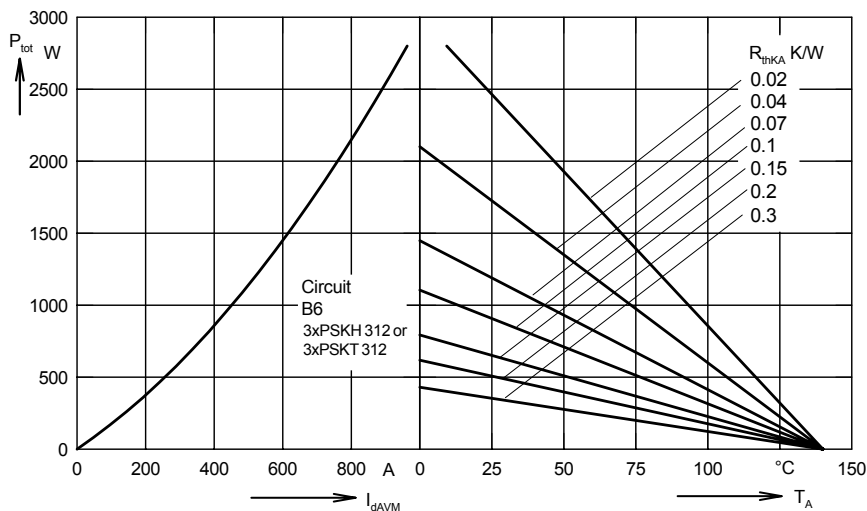


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

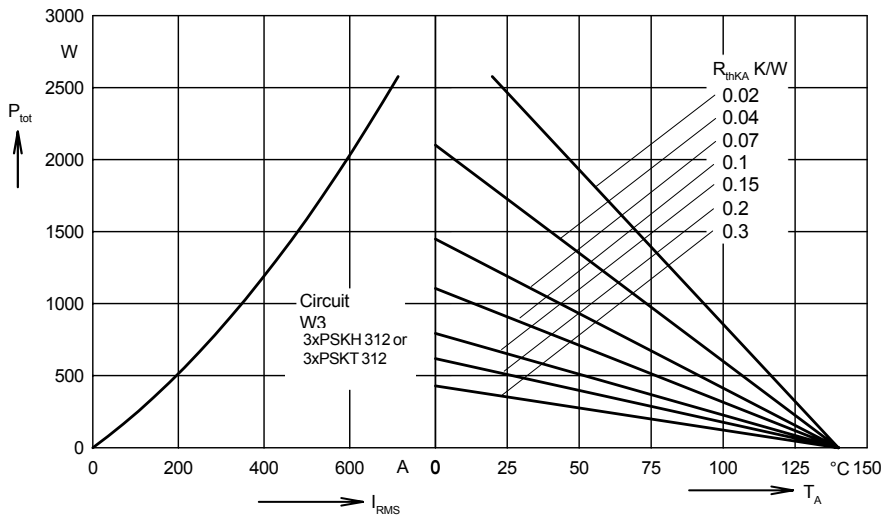


Fig. 7 Three phase AC-controller:
Power dissipation versus RMS
output current and ambient
temperature

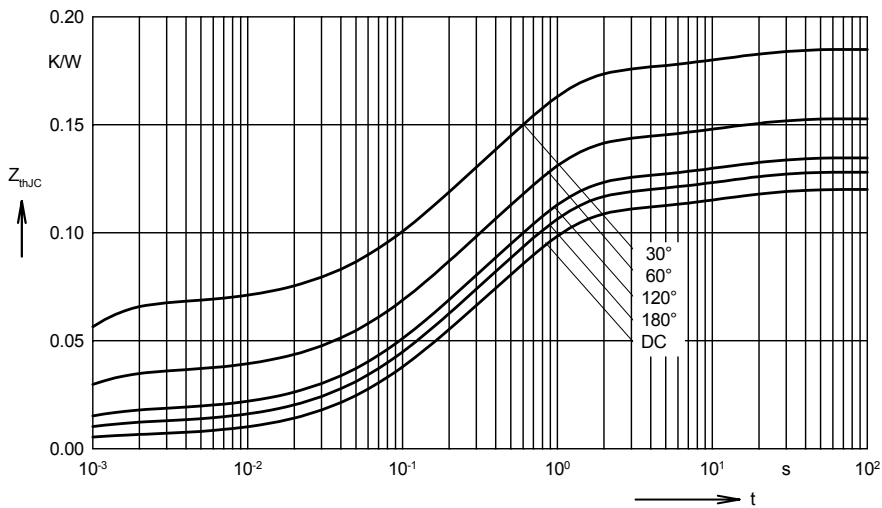


Fig. 8 Transient thermal impedance
junction to case (per thyristor or
diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.120
180°	0.128
120°	0.135
60°	0.153
30°	0.185

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0058	0.00054
2	0.031	0.098
3	0.072	0.54
4	0.0112	12

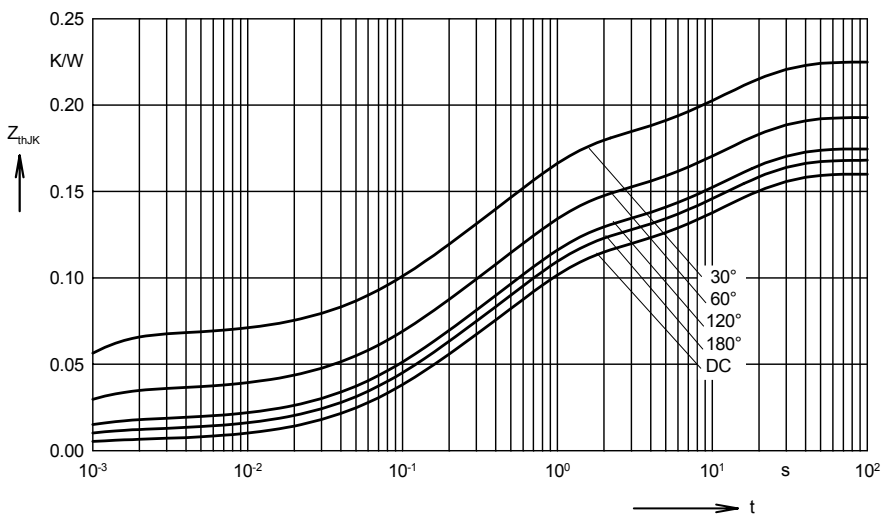


Fig. 9 Transient thermal impedance
junction to heatsink (per thyristor
or diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.160
180°	0.168
120°	0.175
60°	0.193
30°	0.225

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0058	0.00054
2	0.031	0.098
3	0.072	0.54
4	0.0112	12
5	0.04	12